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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	177
Number of Gates	600000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p600-fgg256

ProASIC3 Device Family Overview

ProASIC3 DC and Switching Characteristics

Pin Descriptions

Package Pin Assignments

Datasheet Information

I/Os with Advanced I/O Standards

The ProASIC3 family of FPGAs features a flexible I/O structure, supporting a range of voltages (1.5 V, 1.8 V, 2.5 V, and 3.3 V). ProASIC3 FPGAs support many different I/O standards—single-ended and differential.

The I/Os are organized into banks, with two or four banks per device. The configuration of these banks determines the I/O standards supported (Table 1-1).

Table 1-1 • I/O Standards Supported

		I/O Standards Supported		
I/O Bank Type	**Device and Bank Location**	**LVTTL/ LVCMOS**	**PCI/PCI-X**	**LVPECL, LVDS, B-LVDS, M-LVDS**
Advanced	East and west Banks of A3P250 and larger devices	✓	✓	✓
Standard Plus	North and south banks of A3P250 and larger devices All banks of A3P060 and A3P125	✓	✓	Not supported
Standard	All banks of A3P015 and A3P030	✓	Not supported	Not supported

Each I/O module contains several input, output, and enable registers. These registers allow the implementation of the following:

- Single-Data-Rate applications
- Double-Data-Rate applications—DDR LVDS, B-LVDS, and M-LVDS I/Os for point-to-point communications

ProASIC3 banks for the A3P250 device and above support LVPECL, LVDS, B-LVDS and M-LVDS. B-LVDS and M-LVDS can support up to 20 loads.

Hot-swap (also called hot-plug, or hot-insertion) is the operation of hot-insertion or hot-removal of a card in a powered-up system.

Cold-sparing (also called cold-swap) refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Wide Range I/O Support

ProASIC3 devices support JEDEC-defined wide range I/O operation. ProASIC3 supports the JESD8-B specification, covering both 3 V and 3.3 V supplies, for an effective operating range of 2.7 V to 3.6 V.

Wider I/O range means designers can eliminate power supplies or power conditioning components from the board or move to less costly components with greater tolerances. Wide range eases I/O bank management and provides enhanced protection from system voltage spikes, while providing the flexibility to easily run custom voltage applications.

Specifying I/O States During Programming

You can modify the I/O states during programming in FlashPro. In FlashPro, this feature is supported for PDB files generated from Designer v8.5 or greater. See the *FlashPro User's Guide* for more information.

Note: PDB files generated from Designer v8.1 to Designer v8.4 (including all service packs) have limited display of Pin Numbers only.

1. Load a PDB from the FlashPro GUI. You must have a PDB loaded to modify the I/O states during programming.
2. From the FlashPro GUI, click PDB Configuration. A FlashPoint – Programming File Generator window appears.
3. Click the Specify I/O States During Programming button to display the Specify I/O States During Programming dialog box.
4. Sort the pins as desired by clicking any of the column headers to sort the entries by that header. Select the I/Os you wish to modify (Figure 1-4 on page 1-8).
5. Set the I/O Output State. You can set Basic I/O settings if you want to use the default I/O settings for your pins, or use Custom I/O settings to customize the settings for each pin. Basic I/O state settings:

    1 – I/O is set to drive out logic High

Table 2-15 • **Different Components Contributing to the Static Power Consumption in ProASIC3 Devices**

Parameter	Definition	Device Specific Static Power (mW)							
		A3P1000	A3P600	A3P400	A3P250	A3P125	A3P060	A3P030	A3P015
PDC1	Array static power in Active mode	See Table 2-7 on page 2-7.							
PDC2	I/O input pin static power (standard-dependent)	See Table 2-8 on page 2-7 through Table 2-10 on page 2-8.							
PDC3	I/O output pin static power (standard-dependent)	See Table 2-11 on page 2-9 through Table 2-13 on page 2-10.							
PDC4	Static PLL contribution	2.55 mW							
PDC5	Bank quiescent power (VCCI-dependent)	See Table 2-7 on page 2-7.							

Note: *For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi Power spreadsheet calculator or SmartPower tool in Libero SoC software.*

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-16 on page 2-14.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-17 on page 2-14.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-17 on page 2-14. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption—P_{TOTAL}

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

$P_{STAT} = P_{DC1} + N_{INPUTS}* P_{DC2} + N_{OUTPUTS}* P_{DC3}$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

Total Dynamic Power Consumption—P_{DYN}

$P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$

Global Clock Contribution—P_{CLOCK}

$P_{CLOCK} = (P_{AC1} + N_{SPINE}*P_{AC2} + N_{ROW}*P_{AC3} + N_{S-CELL}* P_{AC4}) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3 FPGA Fabric User's Guide.*

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3 FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

P_{AC1}, P_{AC2}, P_{AC3}, and P_{AC4} are device-dependent.

Sequential Cells Contribution—P_{S-CELL}

$P_{S-CELL} = N_{S-CELL} * (P_{AC5} + \alpha_1 / 2 * P_{AC6}) * F_{CLK}$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-16 on page 2-14.

F_{CLK} is the global clock signal frequency.

Combinatorial Cells Contribution—P_{C-CELL}

$P_{C-CELL} = N_{C-CELL} * \alpha_1 / 2 * P_{AC7} * F_{CLK}$

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-16 on page 2-14.

F_{CLK} is the global clock signal frequency.

Routing Net Contribution—P_{NET}

$P_{NET} = (N_{S-CELL} + N_{C-CELL}) * \alpha_1 / 2 * P_{AC8} * F_{CLK}$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-16 on page 2-14.

F_{CLK} is the global clock signal frequency.

I/O Input Buffer Contribution—P_{INPUTS}

$P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * P_{AC9} * F_{CLK}$

N_{INPUTS} is the number of I/O input buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-16 on page 2-14.

F_{CLK} is the global clock signal frequency.

I/O Output Buffer Contribution—$P_{OUTPUTS}$

$P_{OUTPUTS} = N_{OUTPUTS} * \alpha_2 / 2 * \beta_1 * P_{AC10} * F_{CLK}$

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-16 on page 2-14.

β_1 is the I/O buffer enable rate—guidelines are provided in Table 2-17 on page 2-14.
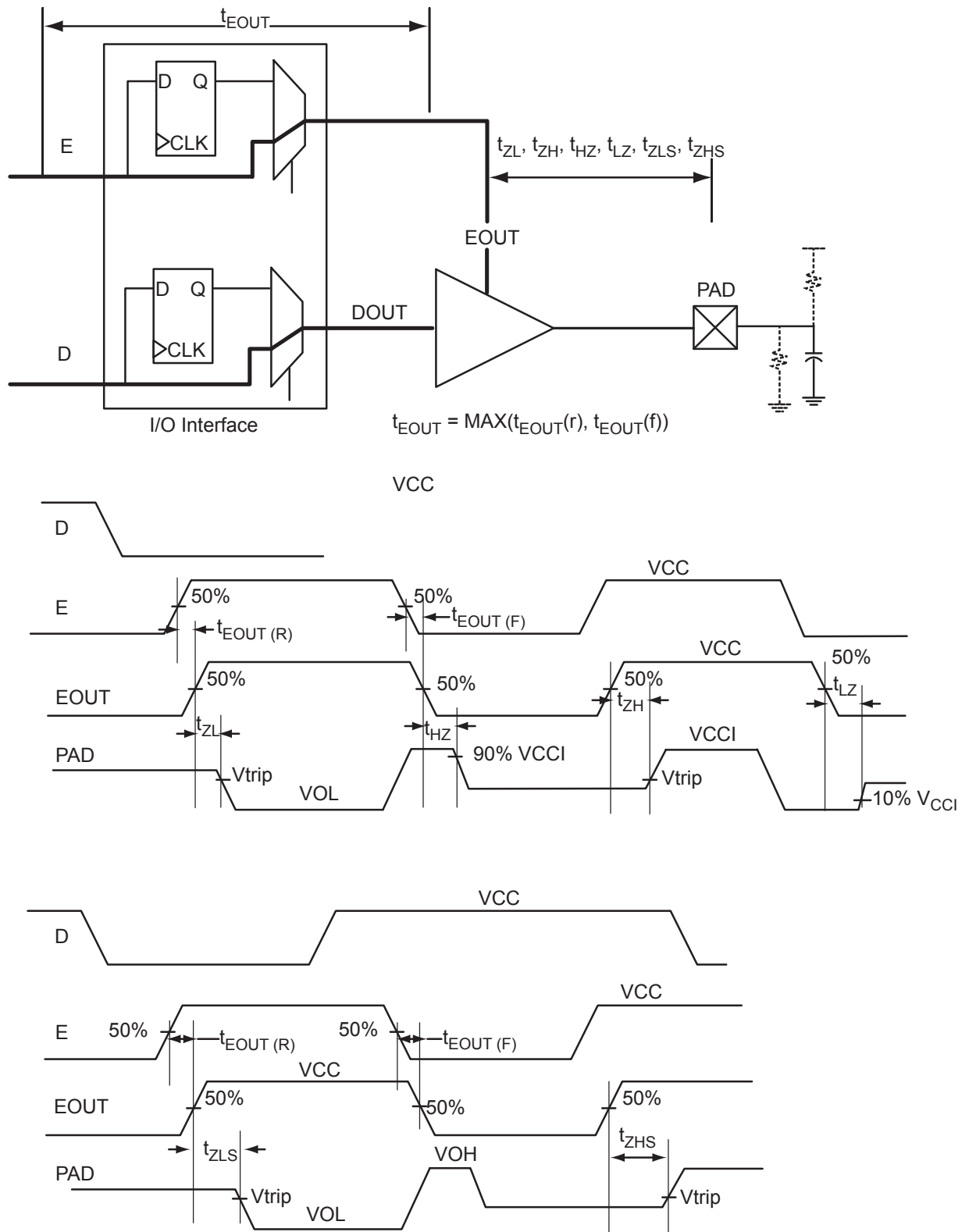
F_{CLK} is the global clock signal frequency.

Figure 2-6 • **Tristate Output Buffer Timing Model and Delays (Example)**

Table 2-25 • **Summary of I/O Timing Characteristics—Software Default Settings**
–2 Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst Case VCC = 1.425 V,
Worst-Case VCCI (per standard)
Standard Plus I/O Banks

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option[1]	Slew Rate	Capacitive Load (pF)	External Resistor	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	35	–	0.45	2.36	0.03	0.75	0.32	2.40	1.93	2.08	2.41	4.07	3.60	ns
3.3 V LVCMOS Wide Range[2]	100 µA	12 mA	High	35	–	0.45	3.65	0.03	1.14	0.32	3.65	2.93	3.22	3.72	6.18	5.46	ns
2.5 V LVCMOS	12 mA	12 mA	High	35	–	0.45	2.39	0.03	0.97	0.32	2.44	2.35	2.11	2.32	4.11	4.02	ns
1.8 V LVCMOS	8 mA	8 mA	High	35	–	0.45	3.03	0.03	0.90	0.32	2.87	3.03	2.19	2.32	4.54	4.70	ns
1.5 V LVCMOS	4 mA	4 mA	High	35	–	0.45	3.61	0.03	1.06	0.32	3.35	3.61	2.26	2.34	5.02	5.28	ns
3.3 V PCI	Per PCI spec	–	High	10	25 [4]	0.45	1.72	0.03	0.64	0.32	1.76	1.27	2.08	2.41	3.42	2.94	ns
3.3 V PCI-X	Per PCI-X spec	–	High	10	25 [4]	0.45	1.72	0.03	0.62	0.32	1.76	1.27	2.08	2.41	3.42	2.94	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
4. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-11 on page 2-64 for connectivity. This resistor is not required during normal operation.*

Table 2-43 • **3.3 V LVTTL / 3.3 V LVCMOS High Slew**
Commercial-Case Conditions: T$_J$ = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t$_{DOUT}$	t$_{DP}$	t$_{DIN}$	t$_{PY}$	t$_{EOUT}$	t$_{ZL}$	t$_{ZH}$	t$_{LZ}$	t$_{HZ}$	t$_{ZLS}$	t$_{ZHS}$	Units
2 mA	Std.	0.66	7.20	0.04	1.00	0.43	7.34	6.29	2.27	2.34	9.57	8.52	ns
	−1	0.56	6.13	0.04	0.85	0.36	6.24	5.35	1.93	1.99	8.14	7.25	ns
	−2	0.49	5.38	0.03	0.75	0.32	5.48	4.69	1.70	1.75	7.15	6.36	ns
4 mA	Std.	0.66	7.20	0.04	1.00	0.43	7.34	6.29	2.27	2.34	9.57	8.52	ns
	−1	0.56	6.13	0.04	0.85	0.36	6.24	5.35	1.93	1.99	8.14	7.25	ns
	−2	0.49	5.38	0.03	0.75	0.32	5.48	4.69	1.70	1.75	7.15	6.36	ns
6 mA	Std.	0.66	4.50	0.04	1.00	0.43	4.58	3.82	2.58	2.88	6.82	6.05	ns
	−1	0.56	3.83	0.04	0.85	0.36	3.90	3.25	2.19	2.45	5.80	5.15	ns
	−2	0.49	3.36	0.03	0.75	0.32	3.42	2.85	1.92	2.15	5.09	4.52	ns
8 mA	Std.	0.66	4.50	0.04	1.00	0.43	4.58	3.82	2.58	2.88	6.82	6.05	ns
	−1	0.56	3.83	0.04	0.85	0.36	3.90	3.25	2.19	2.45	5.80	5.15	ns
	−2	0.49	3.36	0.03	0.75	0.32	3.42	2.85	1.92	2.15	5.09	4.52	ns
12 mA	Std.	0.66	3.16	0.04	1.00	0.43	3.22	2.58	2.79	3.22	5.45	4.82	ns
	−1	0.56	2.69	0.04	0.85	0.36	2.74	2.20	2.37	2.74	4.64	4.10	ns
	−2	0.49	2.36	0.03	0.75	0.32	2.40	1.93	2.08	2.41	4.07	3.60	ns
16 mA	Std.	0.66	3.16	0.04	1.00	0.43	3.22	2.58	2.79	3.22	5.45	4.82	ns
	−1	0.56	2.69	0.04	0.85	0.36	2.74	2.20	2.37	2.74	4.64	4.10	ns
	−2	0.49	2.36	0.03	0.75	0.32	2.40	1.93	2.08	2.41	4.07	3.60	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-45 • **3.3 V LVTTL / 3.3 V LVCMOS High Slew**
Commercial-Case Conditions: T$_J$ = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t$_{DOUT}$	t$_{DP}$	t$_{DIN}$	t$_{PY}$	t$_{EOUT}$	t$_{ZL}$	t$_{ZH}$	t$_{LZ}$	t$_{HZ}$	Units
	–2	0.49	3.29	0.03	0.75	0.32	3.36	2.80	1.79	2.01	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-46 • **3.3 V LVTTL / 3.3 V LVCMOS Low Slew**
Commercial-Case Conditions: T$_J$ = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t$_{DOUT}$	t$_{DP}$	t$_{DIN}$	t$_{PY}$	t$_{EOUT}$	t$_{ZL}$	t$_{ZH}$	t$_{LZ}$	t$_{HZ}$	Units
2 mA	Std.	0.66	9.46	0.04	1.00	0.43	9.64	8.54	2.07	2.04	ns
	–1	0.56	8.05	0.04	0.85	0.36	8.20	7.27	1.76	1.73	ns
	–2	0.49	7.07	0.03	0.75	0.32	7.20	6.38	1.55	1.52	ns
4 mA	Std.	0.66	9.46	0.04	1.00	0.43	9.64	8.54	2.07	2.04	ns
	–1	0.56	8.05	0.04	0.85	0.36	8.20	7.27	1.76	1.73	ns
	–2	0.49	7.07	0.03	0.75	0.32	7.20	6.38	1.55	1.52	ns
6 mA	Std.	0.66	6.57	0.04	1.00	0.43	6.69	5.98	2.40	2.57	ns
	–1	0.56	5.59	0.04	0.85	0.36	5.69	5.09	2.04	2.19	ns
	–2	0.49	4.91	0.03	0.75	0.32	5.00	4.47	1.79	1.92	ns
8 mA	Std.	0.66	6.57	0.04	1.00	0.43	6.69	5.98	2.40	2.57	ns
	–1	0.56	5.59	0.04	0.85	0.36	5.69	5.09	2.04	2.19	ns
	–2	0.49	4.91	0.03	0.75	0.32	5.00	4.47	1.79	1.92	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

3.3 V LVCMOS Wide Range

Table 2-47 • **Minimum and Maximum DC Input and Output Levels**
Applicable to Advanced I/O Banks

3.3 V LVCMOS Wide Range Drive Strength	Equiv. Software Default Drive Strength Option[1]	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
		Min V	Max V	Min V	Max V	Max V	Min V	µA	µA	Max mA[4]	Max mA[4]	µA[5]	µA[5]
100 µA	2 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	4 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	6 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	8 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	12 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	103	109	10	10
100 µA	16 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	132	127	10	10
100 µA	24 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	268	181	10	10

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
4. *Currents are measured at 85°C junction temperature.*
5. *All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*
6. *Software default selection highlighted in gray.*

Table 2-48 • **Minimum and Maximum DC Input and Output Levels**
Applicable to Standard Plus I/O Banks

3.3 V LVCMOS Wide Range Drive Strength	Equiv. Software Default Drive Strength Option[1]	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
		Min V	Max V	Min V	Max V	Max V	Min V	µA	µA	Max mA[4]	Max mA[4]	µA[5]	µA[5]
100 µA	2 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	4 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	6 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	8 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	12 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	103	109	10	10
100 µA	16 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	103	109	10	10

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
4. *Currents are measured at 85°C junction temperature.*
5. *All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*
6. *Software default selection highlighted in gray.*

Output DDR Module
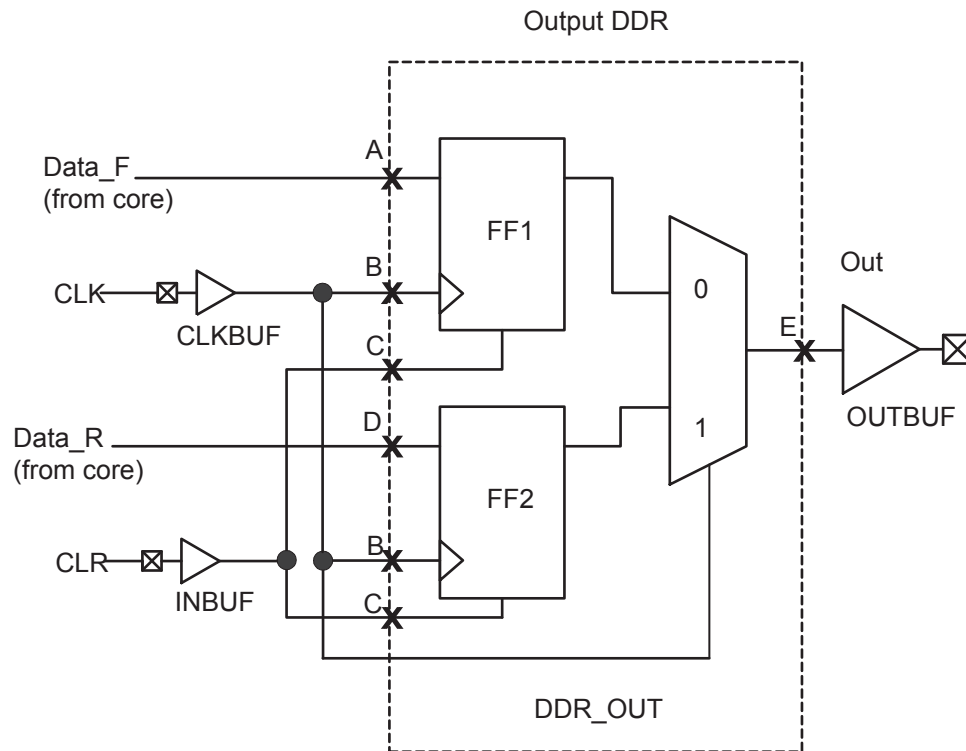
Figure 2-22 • **Output DDR Timing Model**

Table 2-103 • **Parameter Definitions**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
$t_{DDROCLKQ}$	Clock-to-Out	B, E
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out	C, E
$t_{DDROREMCLR}$	Clear Removal	C, B
$t_{DDRORECCLR}$	Clear Recovery	C, B
$t_{DDROSUD1}$	Data Setup Data_F	A, B
$t_{DDROSUD2}$	Data Setup Data_R	D, B
$t_{DDROHD1}$	Data Hold Data_F	A, B
$t_{DDROHD2}$	Data Hold Data_R	D, B

Table 2-123 • **A3P250 FIFO 4k×1 (continued)**
Worst Commercial-Case Conditions: T$_J$ = 70°C, VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t$_{RSTAF}$	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
t$_{RSTBQ}$	RESET Low to Data Out Low on DO (pass-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on DO (pipelined)	0.92	1.05	1.23	ns
t$_{REMRSTB}$	RESET Removal	0.29	0.33	0.38	ns
t$_{RECRSTB}$	RESET Recovery	1.50	1.71	2.01	ns
t$_{MPWRSTB}$	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
t$_{CYC}$	Clock Cycle Time	3.23	3.68	4.32	ns
F$_{MAX}$	Maximum Frequency	310	272	231	MHz

Embedded FlashROM Characteristics
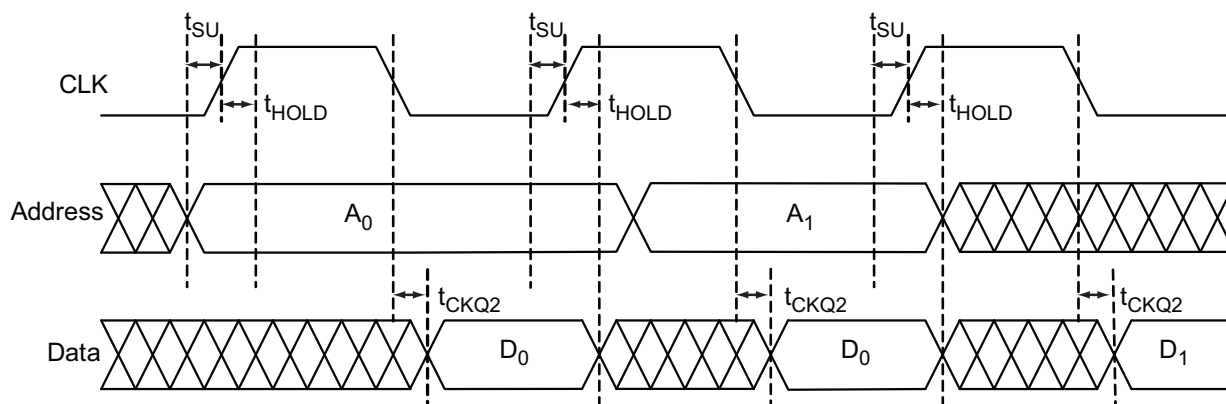
Figure 2-44 • **Timing Diagram**

Timing Characteristics

Table 2-124 • **Embedded FlashROM Access Time**

Parameter	Description	–2	–1	Std.	Units
t$_{SU}$	Address Setup Time	0.53	0.61	0.71	ns
t$_{HOLD}$	Address Hold Time	0.00	0.00	0.00	ns
t$_{CK2Q}$	Clock to Out	21.42	24.40	28.68	ns
F$_{MAX}$	Maximum Clock Frequency	15	15	15	MHz

QN132	
Pin Number	**A3P250 Function**
C17	IO74RSB2
C18	VCCIB2
C19	TCK
C20	VMV2
C21	VPUMP
C22	VJTAG
C23	VCCIB1
C24	IO53NSB1
C25	IO51NPB1
C26	GCA1/IO50PPB1
C27	GCC0/IO48NDB1
C28	VCCIB1
C29	IO42NDB1
C30	GNDQ
C31	GBA1/IO40RSB0
C32	GBB0/IO37RSB0
C33	VCC
C34	IO24RSB0
C35	IO19RSB0
C36	IO16RSB0
C37	IO10RSB0
C38	VCCIB0
C39	GAB1/IO03RSB0
C40	VMV0
D1	GND
D2	GND
D3	GND
D4	GND

VQ100			VQ100			VQ100	
Pin Number	A3P125 Function		Pin Number	A3P125 Function		Pin Number	A3P125 Function
1	GND		37	VCC		73	GBA2/IO41RSB0
2	GAA2/IO67RSB1		38	GND		74	VMV0
3	IO68RSB1		39	VCCIB1		75	GNDQ
4	GAB2/IO69RSB1		40	IO87RSB1		76	GBA1/IO40RSB0
5	IO132RSB1		41	IO84RSB1		77	GBA0/IO39RSB0
6	GAC2/IO131RSB1		42	IO81RSB1		78	GBB1/IO38RSB0
7	IO130RSB1		43	IO75RSB1		79	GBB0/IO37RSB0
8	IO129RSB1		44	GDC2/IO72RSB1		80	GBC1/IO36RSB0
9	GND		45	GDB2/IO71RSB1		81	GBC0/IO35RSB0
10	GFB1/IO124RSB1		46	GDA2/IO70RSB1		82	IO32RSB0
11	GFB0/IO123RSB1		47	TCK		83	IO28RSB0
12	VCOMPLF		48	TDI		84	IO25RSB0
13	GFA0/IO122RSB1		49	TMS		85	IO22RSB0
14	VCCPLF		50	VMV1		86	IO19RSB0
15	GFA1/IO121RSB1		51	GND		87	VCCIB0
16	GFA2/IO120RSB1		52	VPUMP		88	GND
17	VCC		53	NC		89	VCC
18	VCCIB1		54	TDO		90	IO15RSB0
19	GEC0/IO111RSB1		55	TRST		91	IO13RSB0
20	GEB1/IO110RSB1		56	VJTAG		92	IO11RSB0
21	GEB0/IO109RSB1		57	GDA1/IO65RSB0		93	IO09RSB0
22	GEA1/IO108RSB1		58	GDC0/IO62RSB0		94	IO07RSB0
23	GEA0/IO107RSB1		59	GDC1/IO61RSB0		95	GAC1/IO05RSB0
24	VMV1		60	GCC2/IO59RSB0		96	GAC0/IO04RSB0
25	GNDQ		61	GCB2/IO58RSB0		97	GAB1/IO03RSB0
26	GEA2/IO106RSB1		62	GCA0/IO56RSB0		98	GAB0/IO02RSB0
27	GEB2/IO105RSB1		63	GCA1/IO55RSB0		99	GAA1/IO01RSB0
28	GEC2/IO104RSB1		64	GCC0/IO52RSB0		100	GAA0/IO00RSB0
29	IO102RSB1		65	GCC1/IO51RSB0			
30	IO100RSB1		66	VCCIB0			
31	IO99RSB1		67	GND			
32	IO97RSB1		68	VCC			
33	IO96RSB1		69	IO47RSB0			
34	IO95RSB1		70	GBC2/IO45RSB0			
35	IO94RSB1		71	GBB2/IO43RSB0			
36	IO93RSB1		72	IO42RSB0			

FG144		FG144		FG144	
Pin Number	**A3P060 Function**	**Pin Number**	**A3P060 Function**	**Pin Number**	**A3P060 Function**
A1	GNDQ	D1	IO91RSB1	G1	GFA1/IO84RSB1
A2	VMV0	D2	IO92RSB1	G2	GND
A3	GAB0/IO04RSB0	D3	IO93RSB1	G3	VCCPLF
A4	GAB1/IO05RSB0	D4	GAA2/IO51RSB1	G4	GFA0/IO85RSB1
A5	IO08RSB0	D5	GAC0/IO06RSB0	G5	GND
A6	GND	D6	GAC1/IO07RSB0	G6	GND
A7	IO11RSB0	D7	GBC0/IO19RSB0	G7	GND
A8	VCC	D8	GBC1/IO20RSB0	G8	GDC1/IO45RSB0
A9	IO16RSB0	D9	GBB2/IO27RSB0	G9	IO32RSB0
A10	GBA0/IO23RSB0	D10	IO18RSB0	G10	GCC2/IO43RSB0
A11	GBA1/IO24RSB0	D11	IO28RSB0	G11	IO31RSB0
A12	GNDQ	D12	GCB1/IO37RSB0	G12	GCB2/IO42RSB0
B1	GAB2/IO53RSB1	E1	VCC	H1	VCC
B2	GND	E2	GFC0/IO88RSB1	H2	GFB2/IO82RSB1
B3	GAA0/IO02RSB0	E3	GFC1/IO89RSB1	H3	GFC2/IO81RSB1
B4	GAA1/IO03RSB0	E4	VCCIB1	H4	GEC1/IO77RSB1
B5	IO00RSB0	E5	IO52RSB1	H5	VCC
B6	IO10RSB0	E6	VCCIB0	H6	IO34RSB0
B7	IO12RSB0	E7	VCCIB0	H7	IO44RSB0
B8	IO14RSB0	E8	GCC1/IO35RSB0	H8	GDB2/IO55RSB1
B9	GBB0/IO21RSB0	E9	VCCIB0	H9	GDC0/IO46RSB0
B10	GBB1/IO22RSB0	E10	VCC	H10	VCCIB0
B11	GND	E11	GCA0/IO40RSB0	H11	IO33RSB0
B12	VMV0	E12	IO30RSB0	H12	VCC
C1	IO95RSB1	F1	GFB0/IO86RSB1	J1	GEB1/IO75RSB1
C2	GFA2/IO83RSB1	F2	VCOMPLF	J2	IO78RSB1
C3	GAC2/IO94RSB1	F3	GFB1/IO87RSB1	J3	VCCIB1
C4	VCC	F4	IO90RSB1	J4	GEC0/IO76RSB1
C5	IO01RSB0	F5	GND	J5	IO79RSB1
C6	IO09RSB0	F6	GND	J6	IO80RSB1
C7	IO13RSB0	F7	GND	J7	VCC
C8	IO15RSB0	F8	GCC0/IO36RSB0	J8	TCK
C9	IO17RSB0	F9	GCB0/IO38RSB0	J9	GDA2/IO54RSB1
C10	GBA2/IO25RSB0	F10	GND	J10	TDO
C11	IO26RSB0	F11	GCA1/IO39RSB0	J11	GDA1/IO49RSB0
C12	GBC2/IO29RSB0	F12	GCA2/IO41RSB0	J12	GDB1/IO47RSB0

FG144		FG144		FG144	
Pin Number	**A3P250 Function**	**Pin Number**	**A3P250 Function**	**Pin Number**	**A3P250 Function**
A1	GNDQ	D1	IO112NDB3	G1	GFA1/IO108PPB3
A2	VMV0	D2	IO112PDB3	G2	GND
A3	GAB0/IO02RSB0	D3	IO116VDB3	G3	VCCPLF
A4	GAB1/IO03RSB0	D4	GAA2/IO118UPB3	G4	GFA0/IO108NPB3
A5	IO16RSB0	D5	GAC0/IO04RSB0	G5	GND
A6	GND	D6	GAC1/IO05RSB0	G6	GND
A7	IO29RSB0	D7	GBC0/IO35RSB0	G7	GND
A8	VCC	D8	GBC1/IO36RSB0	G8	GDC1/IO58UPB1
A9	IO33RSB0	D9	GBB2/IO42PDB1	G9	IO53NDB1
A10	GBA0/IO39RSB0	D10	IO42NDB1	G10	GCC2/IO53PDB1
A11	GBA1/IO40RSB0	D11	IO43NPB1	G11	IO52NDB1
A12	GNDQ	D12	GCB1/IO49PPB1	G12	GCB2/IO52PDB1
B1	GAB2/IO117UDB3	E1	VCC	H1	VCC
B2	GND	E2	GFC0/IO110NDB3	H2	GFB2/IO106PDB3
B3	GAA0/IO00RSB0	E3	GFC1/IO110PDB3	H3	GFC2/IO105PSB3
B4	GAA1/IO01RSB0	E4	VCCIB3	H4	GEC1/IO100PDB3
B5	IO14RSB0	E5	IO118VPB3	H5	VCC
B6	IO19RSB0	E6	VCCIB0	H6	IO79RSB2
B7	IO22RSB0	E7	VCCIB0	H7	IO65RSB2
B8	IO30RSB0	E8	GCC1/IO48PDB1	H8	GDB2/IO62RSB2
B9	GBB0/IO37RSB0	E9	VCCIB1	H9	GDC0/IO58VPB1
B10	GBB1/IO38RSB0	E10	VCC	H10	VCCIB1
B11	GND	E11	GCA0/IO50NDB1	H11	IO54PSB1
B12	VMV1	E12	IO51NDB1	H12	VCC
C1	IO117VDB3	F1	GFB0/IO109NPB3	J1	GEB1/IO99PDB3
C2	GFA2/IO107PPB3	F2	VCOMPLF	J2	IO106NDB3
C3	GAC2/IO116UDB3	F3	GFB1/IO109PPB3	J3	VCCIB3
C4	VCC	F4	IO107NPB3	J4	GEC0/IO100NDB3
C5	IO12RSB0	F5	GND	J5	IO88RSB2
C6	IO17RSB0	F6	GND	J6	IO81RSB2
C7	IO24RSB0	F7	GND	J7	VCC
C8	IO31RSB0	F8	GCC0/IO48NDB1	J8	TCK
C9	IO34RSB0	F9	GCB0/IO49NPB1	J9	GDA2/IO61RSB2
C10	GBA2/IO41PDB1	F10	GND	J10	TDO
C11	IO41NDB1	F11	GCA1/IO50PDB1	J11	GDA1/IO60UDB1
C12	GBC2/IO43PPB1	F12	GCA2/IO51PDB1	J12	GDB1/IO59UDB1

FG484 – Bottom View

A1 Ball Pad Corner
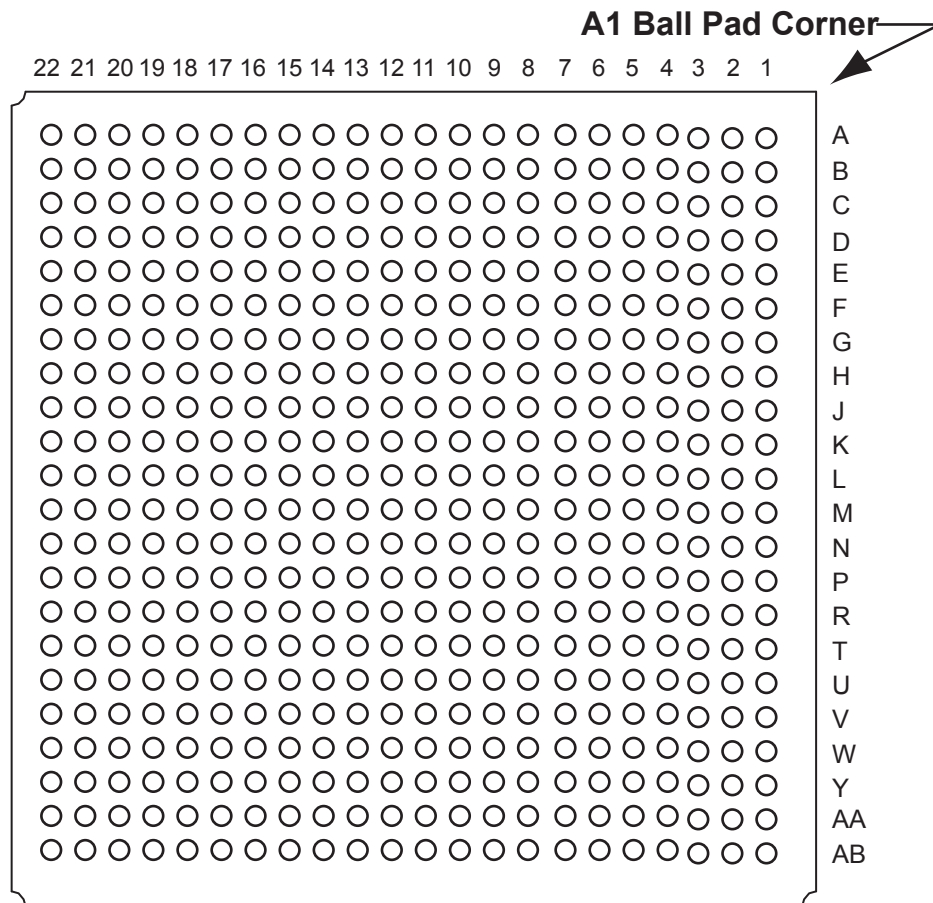
Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

FG484	
Pin Number	**A3P600 Function**
K19	IO75NDB1
K20	NC
K21	IO76NDB1
K22	IO76PDB1
L1	NC
L2	IO155PDB3
L3	NC
L4	GFB0/IO163NPB3
L5	GFA0/IO162NDB3
L6	GFB1/IO163PPB3
L7	VCOMPLF
L8	GFC0/IO164NPB3
L9	VCC
L10	GND
L11	GND
L12	GND
L13	GND
L14	VCC
L15	GCC0/IO69NPB1
L16	GCB1/IO70PPB1
L17	GCA0/IO71NPB1
L18	IO67NPB1
L19	GCB0/IO70NPB1
L20	IO77PDB1
L21	IO77NDB1
L22	IO78NPB1
M1	NC
M2	IO155NDB3
M3	IO158NPB3
M4	GFA2/IO161PPB3
M5	GFA1/IO162PDB3
M6	VCCPLF
M7	IO160NDB3
M8	GFB2/IO160PDB3
M9	VCC
M10	GND

FG484	
Pin Number	**A3P600 Function**
M11	GND
M12	GND
M13	GND
M14	VCC
M15	GCB2/IO73PPB1
M16	GCA1/IO71PPB1
M17	GCC2/IO74PPB1
M18	IO80PPB1
M19	GCA2/IO72PDB1
M20	IO79PPB1
M21	IO78PPB1
M22	NC
N1	IO154NDB3
N2	IO154PDB3
N3	NC
N4	GFC2/IO159PDB3
N5	IO161NPB3
N6	IO156PPB3
N7	IO129RSB2
N8	VCCIB3
N9	VCC
N10	GND
N11	GND
N12	GND
N13	GND
N14	VCC
N15	VCCIB1
N16	IO73NPB1
N17	IO80NPB1
N18	IO74NPB1
N19	IO72NDB1
N20	NC
N21	IO79NPB1
N22	NC
P1	NC
P2	IO153PDB3

FG484	
Pin Number	**A3P600 Function**
P3	IO153NDB3
P4	IO159NDB3
P5	IO156NPB3
P6	IO151PPB3
P7	IO158PPB3
P8	VCCIB3
P9	GND
P10	VCC
P11	VCC
P12	VCC
P13	VCC
P14	GND
P15	VCCIB1
P16	GDB0/IO87NPB1
P17	IO85NDB1
P18	IO85PDB1
P19	IO84PDB1
P20	NC
P21	IO81PDB1
P22	NC
R1	NC
R2	NC
R3	VCC
R4	IO150PDB3
R5	IO151NPB3
R6	IO147NPB3
R7	GEC0/IO146NPB3
R8	VMV3
R9	VCCIB2
R10	VCCIB2
R11	IO117RSB2
R12	IO110RSB2
R13	VCCIB2
R14	VCCIB2
R15	VMV2
R16	IO94RSB2

Revision	Changes	Page
Revision 13 (January 2013)	The "ProASIC3 Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43104).	1-IV
	Added a note to Table 2-2 • Recommended Operating Conditions 1 (SAR 43644): The programming temperature range supported is $T_{ambient}$ = 0°C to 85°C.	2-2
	The note in Table 2-115 • ProASIC3 CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42569).	2-90
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 40284). Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 12 (September 2012)	The Security section was modified to clarify that Microsemi does not support read-back of programmed data.	1-1
	Added a Note stating "VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information" to Table 2-1 • Absolute Maximum Ratings and Table 2-2 • Recommended Operating Conditions 1 (SAR 38321).	2-1 2-2
	Table 2-35 • Duration of Short Circuit Event Before Failure was revised to change the maximum temperature from 110°C to 100°C, with an example of six months instead of three months (SAR 37933).	2-31
	In Table 2-93 • Minimum and Maximum DC Input and Output Levels, VIL and VIH were revised so that the maximum is 3.6 V for all listed values of VCCI (SAR 28549).	2-68
	Figure 2-37 • FIFO Read and Figure 2-38 • FIFO Write are new (SAR 28371).	2-99
	The following sentence was removed from the "VMVx I/O Supply Voltage (quiet)" section in the "Pin Descriptions" chapter: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with "Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks" (SAR 38321). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1

Revision	Changes	Page
Advance v0.3	The "PLL Macro" section was updated. EXTFB information was removed from this section.	2-15
	The CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT} was updated in Table 2-11 • ProASIC3 CCC/PLL Specification	2-29
	EXTFB was removed from Figure 2-27 • CCC/PLL Macro.	2-28
	Table 2-13 • ProASIC3 I/O Features was updated.	2-30
	The "Hot-Swap Support" section was updated.	2-33
	The "Cold-Sparing Support" section was updated.	2-34
	"Electrostatic Discharge (ESD) Protection" section was updated.	2-35
	The LVPECL specification in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices was updated.	2-64
	In the Bank 1 area of Figure 2-72, VMV2 was changed to VMV1 and VCCIB2 was changed to VCC_IB1.	2-97
	The VJTAG and I/O pin descriptions were updated in the "Pin Descriptions" section.	2-50
	The "JTAG Pins" section was updated.	2-51
	"128-Bit AES Decryption" section was updated to include M7 device information.	2-53
	Table 3-6 was updated.	3-6
	Table 3-7 was updated.	3-6
	In Table 3-11, PAC4 was updated.	3-93-8
	Table 3-20 was updated.	3-20
	The note in Table 3-32 was updated.	3-27
	All Timing Characteristics tables were updated from LVTTL to Register Delays	3-31 to 3-73
	The Timing Characteristics for RAM4K9, RAM512X18, and FIFO were updated.	3-85 to 3-90
	F_{TCKMAX} was updated in Table 3-110.	3-97
Advance v0.2	Figure 2-11 was updated.	2-9
	The "Clock Resources (VersaNets)" section was updated.	2-9
	The "VersaNet Global Networks and Spine Access" section was updated.	2-9
	The "PLL Macro" section was updated.	2-15
	Figure 2-27 was updated.	2-28
	Figure 2-20 was updated.	2-19
	Table 2-5 was updated.	2-25
	Table 2-6 was updated.	2-25
	The "FIFO Flag Usage Considerations" section was updated.	2-27
	Table 2-13 was updated.	2-30
	Figure 2-24 was updated.	2-31
	The "Cold-Sparing Support" section is new.	2-34

Revision	Changes	Page
Advance v0.2, (continued)	Table 2-43 was updated.	2-64
	Table 2-18 was updated.	2-45
	Pin descriptions in the "JTAG Pins" section were updated.	2-51
	The "User I/O Naming Convention" section was updated.	2-48
	Table 3-7 was updated.	3-6
	The "Methodology" section was updated.	3-10
	Table 3-40 and Table 3-39 were updated.	3-33,3-32
	The A3P250 "100-Pin VQFP*" pin table was updated.	4-14
	The A3P250 "208-Pin PQFP*" pin table was updated.	4-23
	The A3P1000 "208-Pin PQFP*" pin table was updated.	4-29
	The A3P250 "144-Pin FBGA*" pin table was updated.	4-36
	The A3P1000 "144-Pin FBGA*" pin table was updated.	4-32
	The A3P250 "256-Pin FBGA*" pin table was updated.	4-45
	The A3P1000 "256-Pin FBGA*" pin table was updated.	4-54
	The A3P1000 "484-Pin FBGA*" pin table was updated.	4-68